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Substitute for Form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	10/763136
Filing Date	January 22, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Nguyen, Tuan

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Attorney Docket No: 303.588US3

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